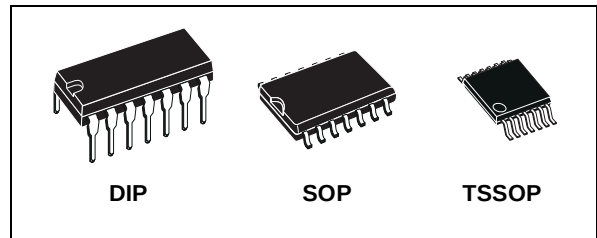


QUAD BILATERAL SWITCH

- HIGH SPEED:
 $t_{PD} = 9ns$ (TYP.) at $V_{CC} = 6V$
- LOW POWER DISSIPATION:
 $I_{CC} = 1\mu A$ (MAX.) at $T_A = 25^\circ C$
- LOW "ON" RESISTANCE:
 $R_{ON} = 60\Omega$ TYP. AT $V_{CC} = 9V$, $I_{I/O} = 100\mu A$
- WIDE OPERATING VOLTAGE RANGE
 V_{CC} (OPR) = 2V TO 12V
- SINE WAVE DISTORTION:
0.042% at $V_{CC} = 9V_{pp}$, $f = 1KHz$
- HIGH NOISE IMMUNITY:
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (MIN.)
- PIN AND FUNCTION COMPATIBLE WITH
74 SERIES 4016

DESCRIPTION

The M74HC4016 is an high speed CMOS QUAD BILATERAL SWITCH fabricated with silicon gate C²MOS technology.

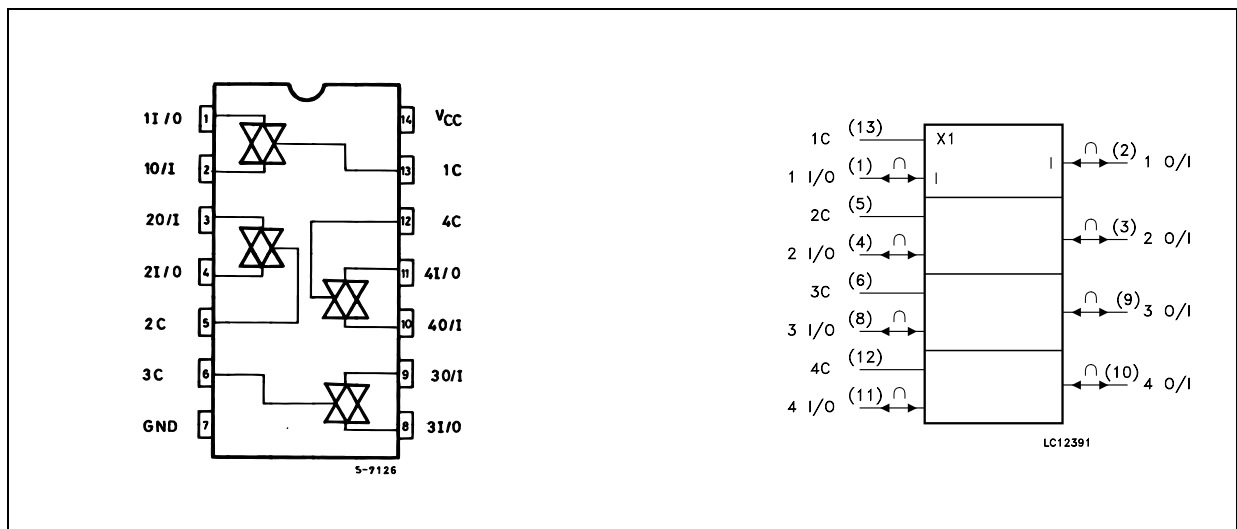


ORDER CODES

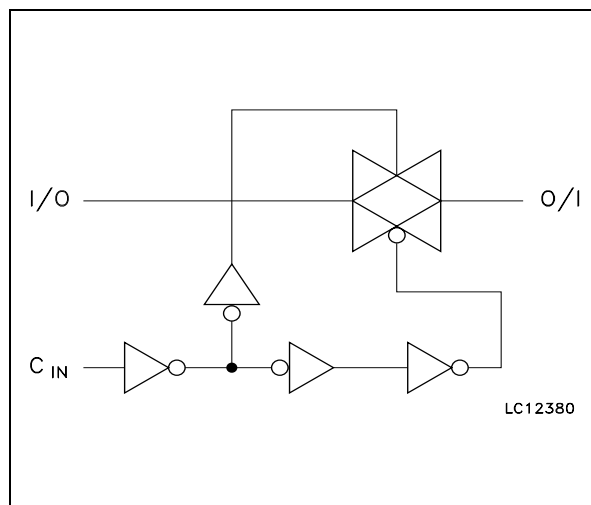
PACKAGE	TUBE	T & R
DIP	M74HC4016B1R	
SOP	M74HC4016M1R	M74HC4016RM13TR
TSSOP		M74HC4016TTR

The C input is provided to control the switch; the switch is on when the C input is held high and off when C is held low.

PIN CONNECTION AND IEC LOGIC SYMBOLS



LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 8, 11	1 to 4 I/O	Independent Inputs/Outputs
2, 3, 9, 10	1 to 4 O/I	Independent Outputs/Inputs
13, 5, 6, 12	1C to 4C	Enable Inputs (Active High)
7	GND	Ground (0V)
14	V _{CC}	Positive Supply Voltage

TRUTH TABLE

CONTROL	SWITCH FUNCTION
H	ON
L	OFF

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +13	V
V _{IN}	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _{I/O}	DC Input/Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{OK}	Control Input DC Diode Current	± 20	mA
I _{I/O}	I/O DC Diode Current	± 20	mA
I _O	DC Output Source Sink Current Per Output Pin	± 25	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
P _D	Power Dissipation	500(*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	2 to 12	V
V _{IN}	Input Voltage (Control)	0 to V _{CC}	V
V _{I/O}	I/O Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature	-55 to 125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 2.0V	0 to 1000
		V _{CC} = 4.5V	0 to 500
		V _{CC} = 6.0V	0 to 400
		V _{CC} = 10.0V	0 to 250

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IHC}	High Level Control Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		9.0		6.3			6.3		6.3		
		12.0		8.4			8.4		8.4		
V _{ILC}	Low Level Control Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		9.0				2.5		2.5		2.5	
		12.0				3.6		3.6		3.6	
R _{ON}	ON Resistance	4.5	V _{IN} = V _{IHC}		160	320		400		450	Ω
		9.0	V _{I/O} = V _{CC} to GND		85	170		213		260	
		12.0	I _{I/O} = 100μA		60	120		150		180	
		4.5	V _{IN} = V _{IHC}		80	160		200		250	
		9.0	V _{I/O} = V _{CC} or GND		60	120		150		200	
		12.0	I _{I/O} = 100μA		50	100		125		150	
ΔR _{ON}	Difference of ON Resistance between switches	4.5	V _{IN} = V _{IHC}		16						Ω
		9.0	V _{I/O} = V _{CC} or GND		9						
		12.0	I _{I/O} ≤ 100μA		6						
I _{OFF}	Input/Output Leakage Current (SWITCH OFF)	12.0	V _{OS} = V _{CC} or GND V _{IS} = V _{CC} or GND V _{IN} = V _{ILC}			± 0.1		± 1		± 2	μA
I _{IZ}	Switch Input Leakage Current (SWITCH ON, OUTPUT OPEN)	12.0	V _{OS} = V _{CC} or GND V _{IN} = V _{IHC}			± 0.1		± 1		± 2	μA
I _{IN}	Control Input Current	6.0	V _{IN} = V _{CC} or GND			± 0.1		± 1		± 1	μA
I _{CC}	Quiescent Supply Current	6.0	V _{IN} = V _{CC} or GND			1		10		20	μA
		9.0				4		40		80	
		12.0				8		80		160	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
Φ _{I/O}	Phase Difference Between Input and Output	2.0			20	50		65		75	ns
		4.5			5	10		13		15	
		9.0			4	8		10		12	
		12.0			3	7		9		11	
t _{PZL} t _{PZH}	Output Enable Time	2.0	R _L = 1KΩ		40	100		125		150	ns
		4.5			10	20		25		30	
		9.0			8	15		20		24	
		12.0			7	14		18		21	
t _{PLZ} t _{PHZ}	Output Disable Time	2.0	R _L = 1KΩ		60	150		190		225	ns
		4.5			15	30		38		45	
		9.0			10	26		33		36	
		12.0			8	24		30		32	

CAPACITIVE CHARACTERISTICS

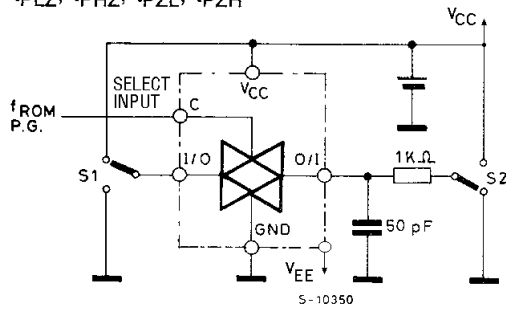
Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance				5	10		10		10	pF
C _{I/O}	Switch Terminal Capacitance				5						pF
C _{IOS}	Feed Through Capacitance				1						pF
C _{PD}	Power Dissipation Capacitance (note 1)				15						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}$

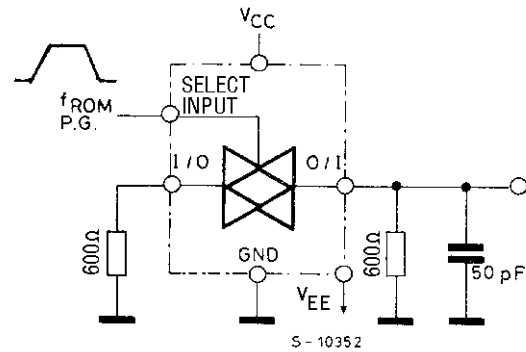
ANALOG SWITCH CHARACTERISTICS (GND = 0V; $T_A = 25^\circ\text{C}$)

Symbol	Parameter	Test Condition		Value	Unit
		V_{CC} (V)	V_{IN} (V_{p-p})	Typ.	
	Sine Wave Distortion (THD)	4.5	4.5	0.118	%
		9.0	9.0	0.042	
		12.0	12.0	0.032	
f_{MAX}	Frequency Response (Switch ON)	4.5	Adjust f_{IN} voltage to obtain 0 dBm at V_{OS} . Increase f_{IN} Frequency until dB meter reads -3dB $R_L = 50\Omega$, $C_L = 50\text{ pF}$	23	MHz
		9.0		38	
		12.0		42	
	Feed through Attenuation (Switch OFF)	4.5	V_{IN} is centered at $V_{CC}/2$. Adjust input for 0 dBm $R_L = 600\Omega$, $C_L = 50\text{ pF}$, $f_{IN} = 1\text{ MHz}$ sine wave	-50	dB
		9.0		-50	
		12.0		-50	
	Crosstalk (Control Input to Signal Output)	4.5	$R_L = 600\Omega$, $C_L = 50\text{ pF}$, $f_{IN} = 1\text{ MHz}$ square wave ($t_r = t_f = 6\text{ ns}$)	8	mV
		9.0		23	
		12.0		40	
	Crosstalk (Between Any Switches)	4.5	Adjust V_{IN} to Obtain 0 dBm at input $R_L = 600\Omega$, $C_L = 50\text{ pF}$, $f_{IN} = 1\text{ MHz}$ sine wave	-50	dB
		9.0		-50	
		12.0		-50	

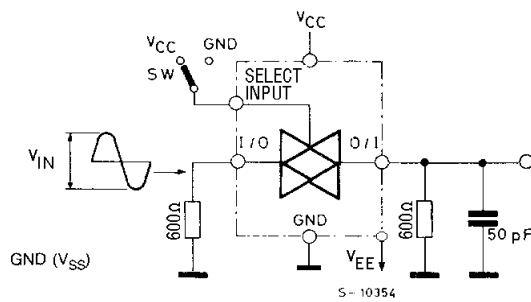
SWITCHING CHARACTERISTICS TEST CIRCUIT

 t_{PLZ} , t_{PHZ} , t_{PZL} , t_{PZH} 

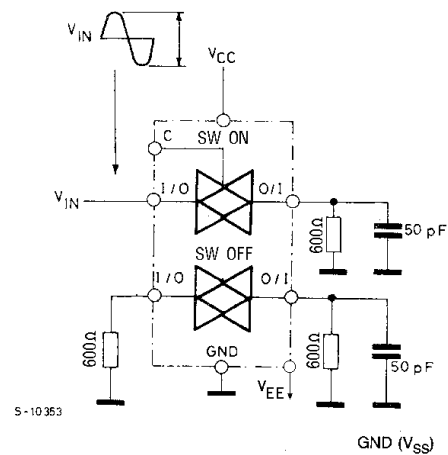
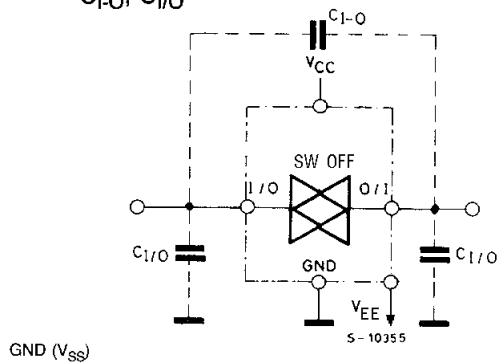
CROSSTALK (control to output)



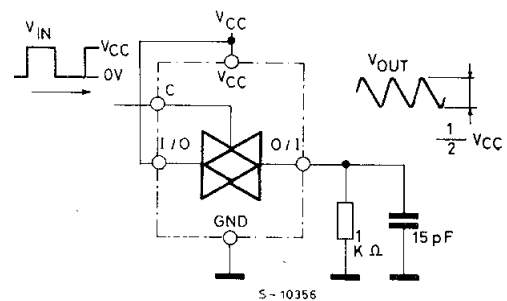
BANDWIDTH AND FEEDTHROUGH ATTENUATION

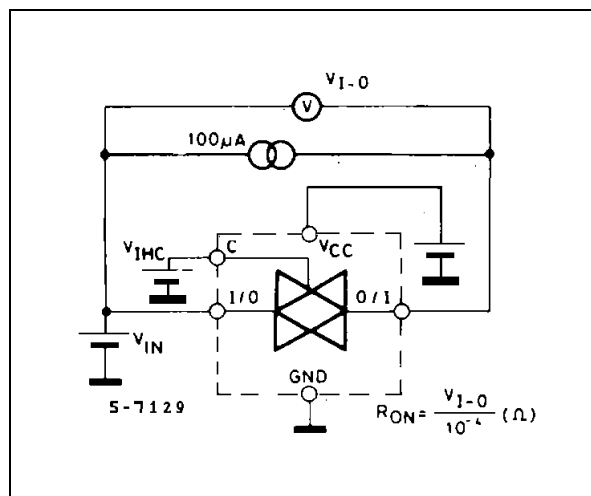
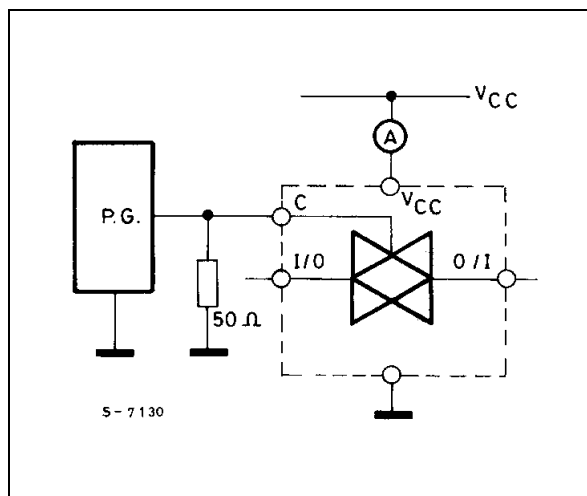


CROSSTALK BETWEEN ANY TWO SWITCHES

 C_{I-O} , $C_{I/O}$ 

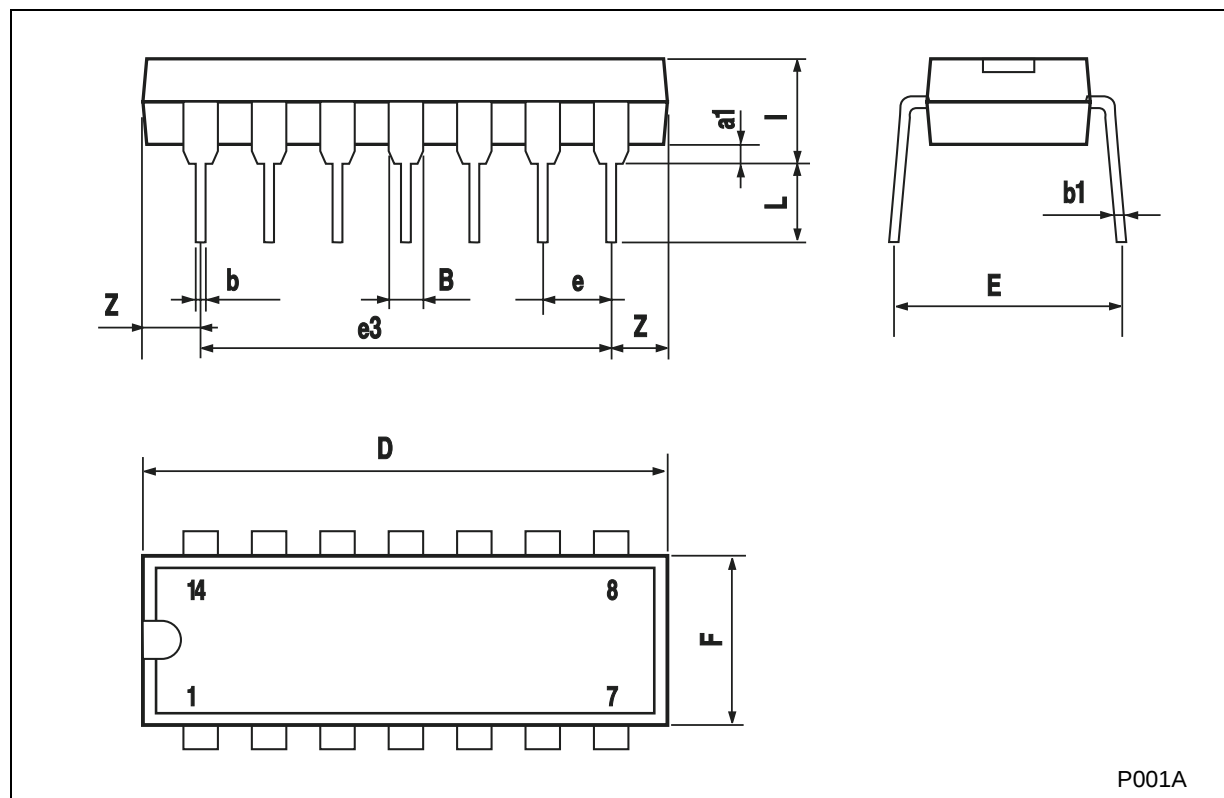
MAXIMUM CONTROL FREQUENCY



CHANNEL RESISTANCE (R_{ON}) I_{CC} (Opr.)

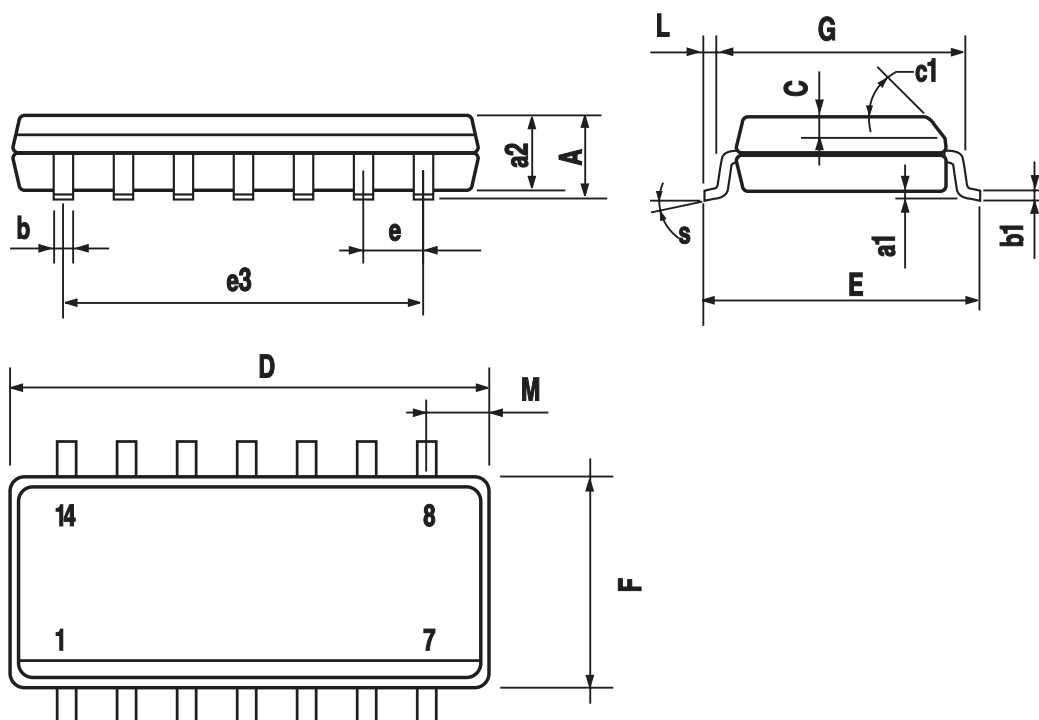
Plastic DIP-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



0080337D

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco
Singapore - Spain - Sweden - Switzerland - United Kingdom

© <http://www.st.com>

